

VOLTAGE DETECTOR

■ GENERAL DESCRIPTION

The NJU7706/07 is a high precision voltage detector with a built-in delay time generator of fixed time.

The NJU7706/07 are useful for preventing malfunction of microcomputer or DSP etc. through detect a drop in voltage of battery or power supply.

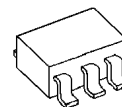
The delay function achieves set wait time when supply voltage is unstable. Moreover, the delay function can make a sequence that other devices in application work and stabilize before microcomputer or DSP works.

The detection voltage is internally fixed with an accuracy of 1.0%, and three fixed delay times 50ms, 100ms and 200ms are available. Manual reset function can output reset signal irrespective of detection voltage.

NJU7706 is Nch. Open Drain and NJU7707 is a C-MOS output type.

Small packaging makes NJU7706 and NJU7707 suitable for space conscious applications.

■ PACKAGE OUTLINE

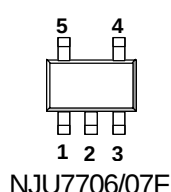


NJU7706/07F

■ FEATURES

- High Precision Detection Voltage $\pm 1.0\%$
- Low Quiescent Current 1.3 μ A typ.
- Detection Voltage Range 1.5 ~ 6.0V(0.1V step)
- Delay Time(Built-in Fixed Type) 50ms /100ms /200ms(Built-in Fixed Type)
- ON/OFF switch of delay time(DS pin)
- Manual Reset
Active "L" : NJU770*F**A
Active "H" : NJU770*F**B
- Output Configuration
NJU7706: Nch. Open Drain type
NJU7707: C-MOS Output type
- Package Outline SOT-23-5

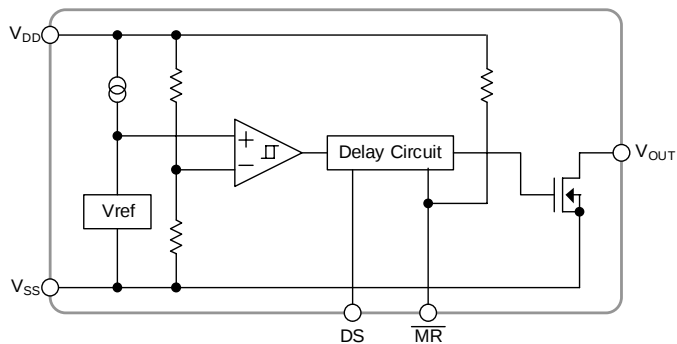
■ PIN CONFIGURATION



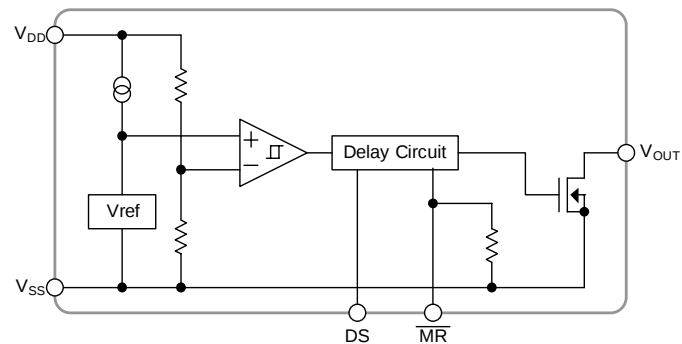
PIN FUNCTION

- 1.DS
- 2.V_{SS}
- 3.MR
- 4.V_{OUT}
- 5.V_{DD}

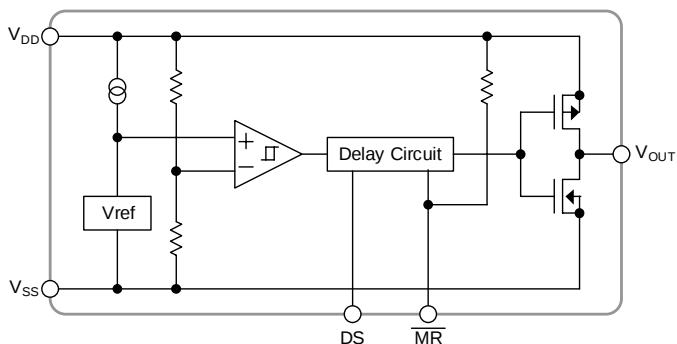
■ EQUIVALENT CIRCUIT



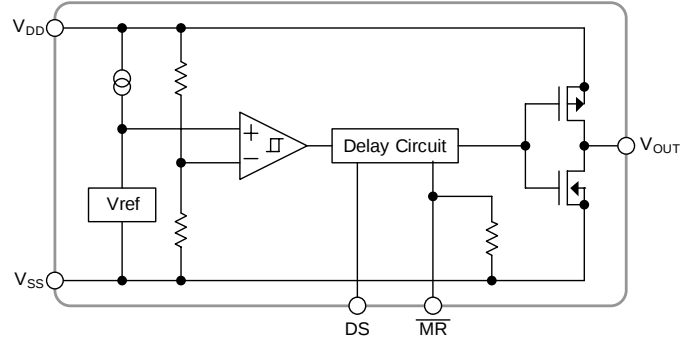
NJU7706**A*



NJU7706**B*



NJU7707**A*



NJU7707**B*

■ DETECTION VOLTAGE RANK LIST

Device Name	V _{DET}	MR Logic	Delay Time
NJM770*F27A1	2.7V	Active “L”	50ms
NJU770*F39A1	3.9V		
NJU770*F42A1	4.2V		
NJM770*F27B1	2.7V	Active “H”	100ms
NJU770*F15A2	1.5V	Active “L”	
NJU770*F19A2	1.9V		
NJU770*F21A2	2.1V		
NJU770*F22A2	2.2V		
NJU770*F25A2	2.5V		
NJU770*F27A2	2.7V		
NJU770*F28A2	2.8V		
NJU770*F29A2	2.9V		
NJU770*F03A2	3.0V		
NJU770*F42A2	4.2V		
NJU770*F43A2	4.3V		
NJU770*F45A2	4.5V		
NJU770*F06A2	6.0V		
NJU770*F25B2	2.5V	Active “H”	
NJU770*F27B2	2.7V		
NJU770*F42B2	4.2V		
NJU770*F27A3	2.7V	Active “L”	200ms
NJU770*F39A3	3.9V		
NJU770*F42A3	4.2V		
NJU770*F27B3	2.7V	Active “H”	

■ NJU7706

■ ABSOLUTE MAXIMUM RATINGS

(Ta=25°C)

PARAMETER	SYMBOL	RATINGS		UNIT
Input Voltage	V _{DD}	+10		V
Output Voltage	V _{OUT}	V _{SS} -0.3 ~ +10		V
Output Current	I _{OUT}	50		mA
Power Dissipation	P _D	SOT-23-5	350(*1) 200(*2)	mW
Operating Temperature	T _{opr}	-40 ~ +85		°C
Storage Temperature	T _{stg}	-40 ~ +125		°C

(*1) : Mounted on glass epoxy board based on EIA/JEDEC. (114.3x76.2x1.6mm: 2Layers)

(*2) : Device itself

■ ELECTRICAL CHARACTERISTICS

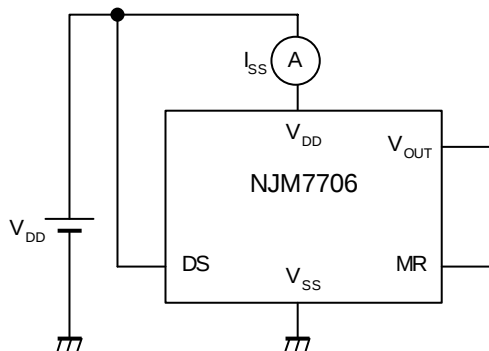
(Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Detection Voltage	V _{DET}			-1.0%	—	+1.0%	V
Hysteresis Voltage	V _{HYS}			70	90	130	mV
Quiescent Current	I _{SS}	V _{DD} =V _{DET} +1V	V _{DET} =1.5V ~ 1.9V Version	—	1.0	1.7	μA
			V _{DET} =2.0V ~ 6.0V Version	—	1.3	2.2	
Output Current	I _{OUT}	Nch, V _{DS} =0.5V	V _{DD} =1.2V	0.75	2.0	—	mA
			V _{DD} =2.4V (≥2.7V Version)	4.5	7.0	—	
Output Leak Current	I _{LEAK}	V _{DD} =V _{OUT} =9V		—	—	0.1	μA
Detection Voltage Temperature Coefficient	Δ V _{DET} /ΔTa	Ta=0 ~ +85°C		—	±100	—	ppm/°C
Delay Time 1	t _{d1}	V _{DD} =V _{DET} +1V, DS="L Level"	NJU7706F***1	42.5	50	57.5	ms
			NJU7706F***2	85	100	115	ms
			NJU7706F***3	170	200	230	ms
Delay Time 2	t _{d2}	V _{DD} =V _{DET} +1V, DS="H Level"		25	100	300	μs
Input Voltage of DS pin	V _{DS_H}			1.5	—	V _{DD}	V
	V _{DS_L}			0	—	0.3	V
Input Voltage of MR pin (Active "L")	V _{MR_H}			1.5	—	V _{DD}	V
	V _{MR_L}			0	—	0.3	V
Input Voltage of MR pin (Active "H")	V _{MR_H}			V _{DD} -0.3	—	V _{DD}	V
	V _{MR_L}			0	—	V _{DD} -1.5	V
Impedance of MR pin	R _{MR}			1.0	2.0	3.0	MΩ
Operating Voltage (*3)	V _{DD}	R _L =100kΩ		0.8	—	9	V

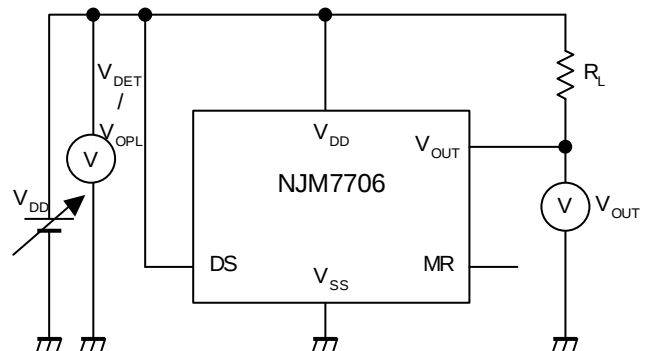
(*3): The minimum operating voltage(V_{OPL}) indicates the same value of the input voltage(V_{DD}) on condition that V_{OUT} becomes 10% or less of the input voltage(V_{DD}).

■ TEST CIRCUIT

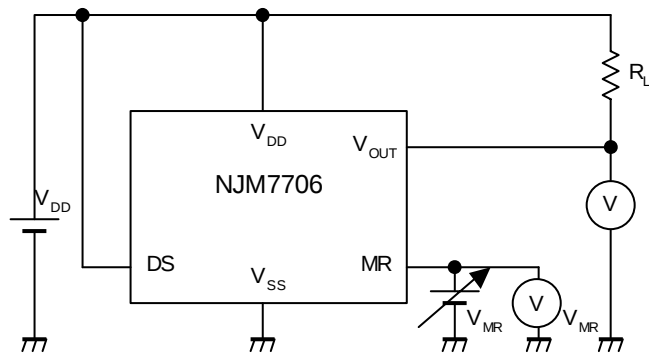
● Circuit Operating Current TEST CIRCUIT



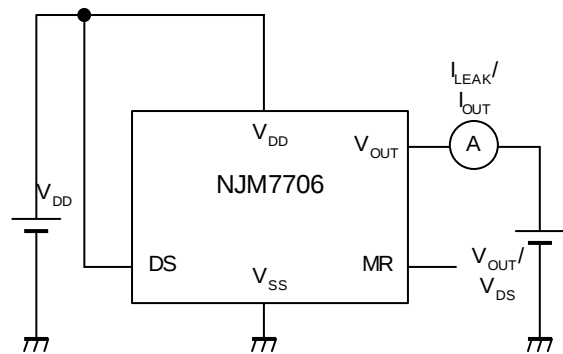
● Detection voltage / Minimum operating voltage TEST CIRCUIT



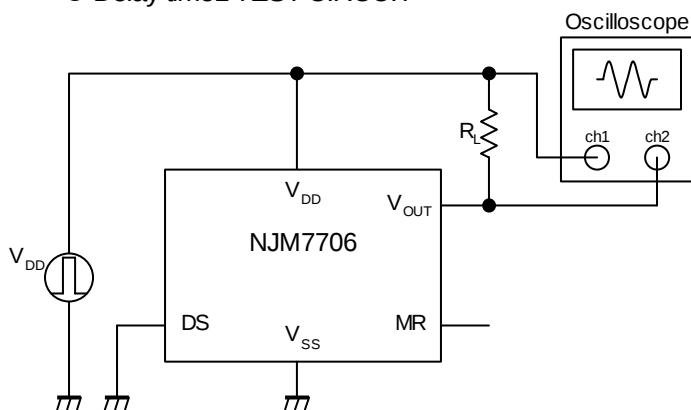
● MR pin Input voltage TEST CIRCUIT



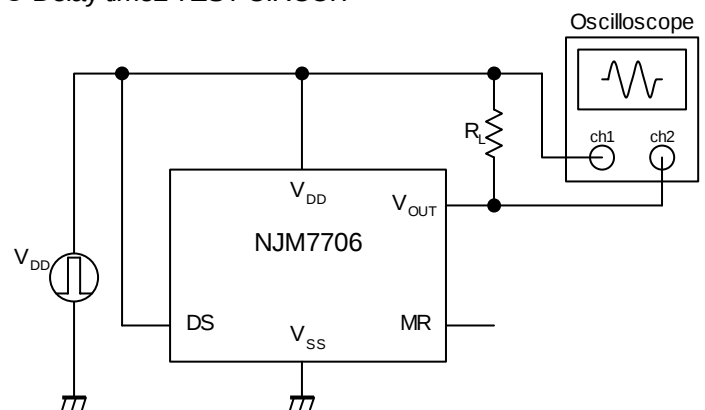
● Leak current / Output current TEST CIRCUIT



● Delay time1 TEST CIRCUIT

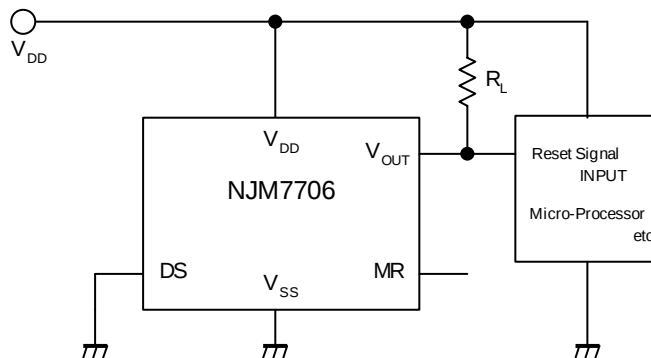


● Delay time2 TEST CIRCUIT

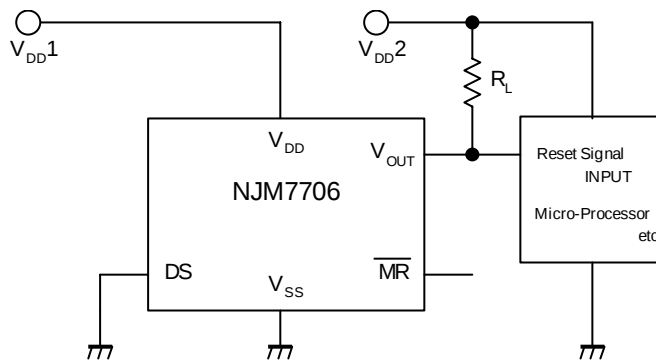


■ TYPICAL APPLICATION

① Power Supply Monitor Circuit (V_{DD} line COMMON)



② Power Supply Monitor Circuit (V_{DD} line SEPARATE)



■ NJU7707

■ ABSOLUTE MAXIMUM RATINGS

(Ta=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Input Voltage	V_{DD}	+10	V
Output Voltage	V_{OUT}	$V_{SS}-0.3 \sim V_{DD}+0.3$	V
Output Current	I_{OUT}	50	mA
Power Dissipation	P_D	SOT-23-5 350(*4) 200(*5)	mW
Operating Temperature	T_{opr}	-40 ~ +85	°C
Storage Temperature	T_{stg}	-40 ~ +125	°C

(*4) : Mounted on glass epoxy board based on EIA/JEDEC. (114.3x76.2x1.6mm: 2Layers)

(*5) : Device itself

■ ELECTRICAL CHARACTERISTICS

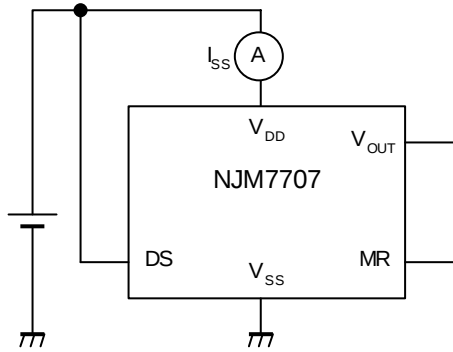
(Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Detection Voltage	V_{DET}		-1.0%	—	+1.0%	V
Hysteresis Voltage	V_{HYS}		70	90	130	mV
Quiescent Current	I_{SS}	$V_{DD}=V_{DET}+1V$ $V_{DET}=1.5V \sim 1.9V$ Version $V_{DET}=2.0V \sim 6.0V$ Version	— —	1.0 1.3	1.7 2.2	μA
Output Current	I_{OUT}	Nch, $V_{DS}=0.5V$ $V_{DD}=1.2V$ $V_{DD}=2.4V$ ($\geq 2.7V$ Version) $V_{DD}=4.8V$ ($\leq 3.9V$ Version) Pch, $V_{DS}=0.5V$ $V_{DD}=6.0V$ (4.0V ~ 5.6V Version) $V_{DD}=8.4V$ ($\geq 5.7V$ Version)	0.75 4.5 2.0 2.5 3.0	2.0 7.0 3.5 4.0 5.0	— — — — —	mA
Detection Voltage Temperature Coefficient	$\Delta V_{DET} / \Delta T_a$	Ta=0 ~ +85°C	—	± 100	—	ppm/°C
Delay Time 1	t_{d1}	$V_{DD}=V_{DET}+1V$, DS="L Level" NJU7707F***1 NJU7707F***2 NJU7707F***3	42.5 85 170	50 100 200	57.5 115 230	ms
Delay Time 2	t_{d2}	$V_{DD}=V_{DET}+1V$, DS="H Level"	25	50	300	μs
Input Voltage of DS pin	V_{DS_H} V_{DS_L}		1.5 0	— —	V_{DD} 0.3	V
Input Voltage of MR pin (Active "L")	V_{MR_H} V_{MR_L}		1.5 0	— —	V_{DD} 0.3	V
Input Voltage of MR pin (Active "H")	V_{MR_H} V_{MR_L}		$V_{DD}-0.3$ 0	— —	V_{DD} $V_{DD}-1.5$	V
Impedance of MR pin	R_{MR}		1.0	2.0	3.0	M Ω
Operating Voltage (*6)	V_{DD}	$R_L=100k\Omega$	0.8	—	9	V

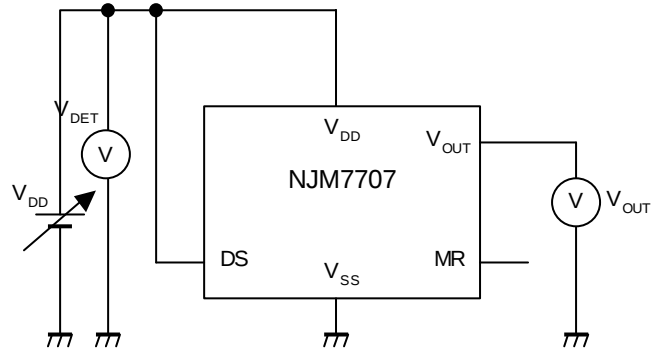
(*6): The minimum operating voltage(V_{OPL}) indicates the same value of the input voltage(V_{DD}) on condition that V_{OUT} becomes 10% or less of the input voltage(V_{DD}).

■ TEST CIRCUIT

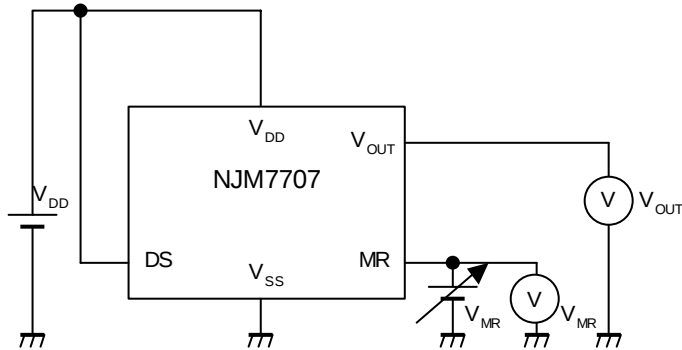
● Circuit Operating Current TEST CIRCUIT



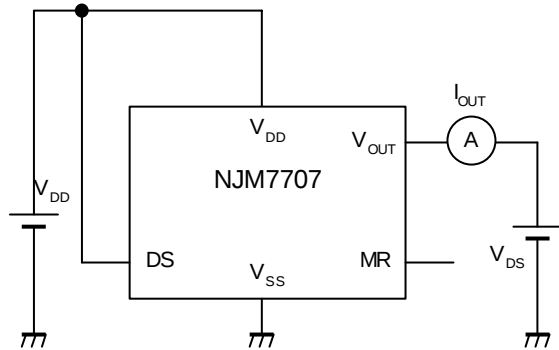
● Detection voltage TEST CIRCUIT



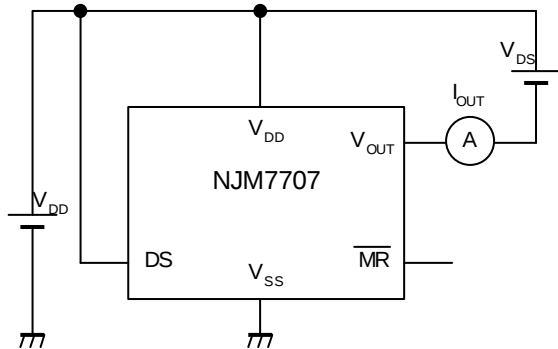
● MR pin Input voltage TEST CIRCUIT



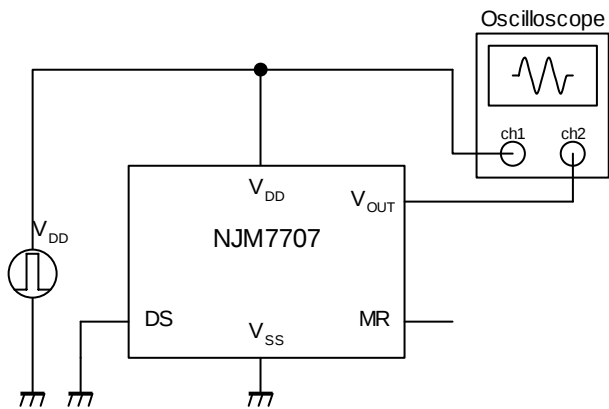
● Nch Output current TEST CIRCUIT



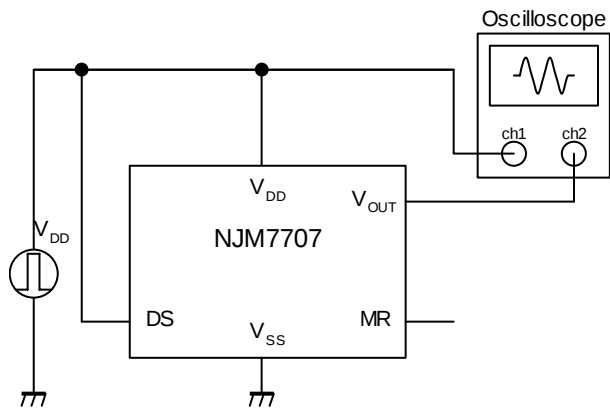
● Pch Output current TEST CIRCUIT



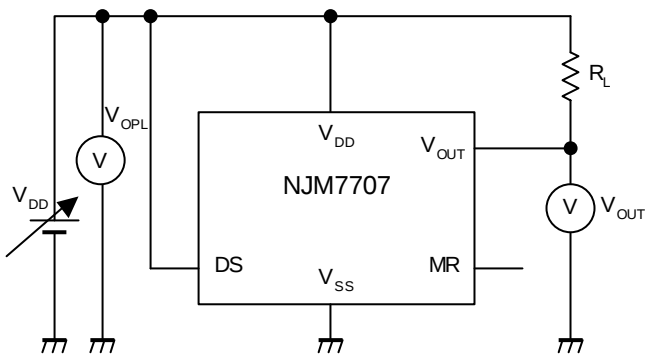
● Delay time1 TEST CIRCUIT



● Delay time2 TEST CIRCUIT

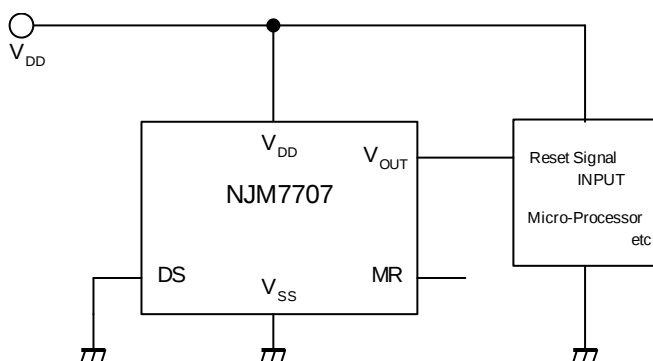


● Minimum operating voltage TEST CIRCUIT



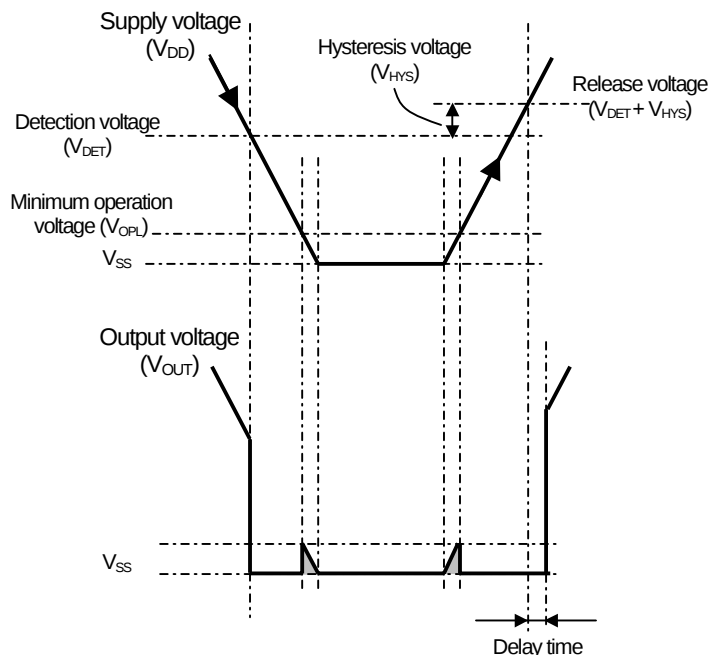
■ TYPICAL APPLICATION

① Power Supply Monitor Circuit (VDD line COMMON)



■ Functional Description

(1) Basic operation



- (1) When supply voltage (V_{DD}) drops below detection voltage (V_{DET}), Output voltage (V_{OUT}) changes "H" to "L" to alert reset state.
- (2) The reset state is kept while V_{DD} is lower than release voltage. The release voltage is a sum of V_{DET} and Hysterisis voltage (V_{HYS}). Please refer to the (*7) below.
- (3) When V_{DD} becomes higher than the release voltage and reset release delay time fixed by internal is past, then V_{OUT} changes from "L" to "H" to resume normal state.

(*7) V_{HYS} is to avoid unstable V_{OUT} state caused by rapid voltage change at nearby V_{DET} .

(*8): C-MOS output product (NJU7707) : When V_{DD} less than V_{OPL} , V_{OUT} is free of the shaded region.

(2) Description of Manual Reset

Reset signal can output independently with MR.

Logic of MR	Operation
Active "L"	$V_{MR} = "L" \Rightarrow$ Reset "ON"
Active "H"	$V_{MR} = "H" \Rightarrow$ Reset "ON"

If Manual Reset is not required, please connect MR terminal as following.

Logic of MR	Connection
Active "L"	Connect MR terminal to V_{DD} or open
Active "H"	Connect MR terminal to GND or open

[CAUTION]

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